

Features

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

Maximum Ratings

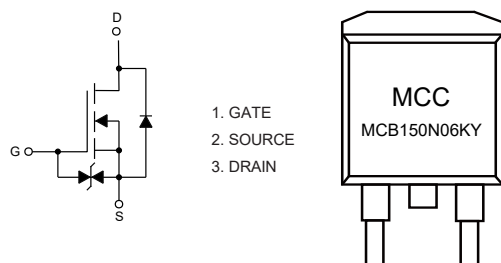
- Operating Junction Temperature Range : -55°C to $+150^{\circ}\text{C}$
- Storage Temperature Range: -55°C to $+150^{\circ}\text{C}$
- Thermal Resistance: 15°C/W Junction to Ambient($t \leq 10\text{S}$)⁽²⁾
- Thermal Resistance: 60°C/W Junction to Ambient(Steady-State)⁽²⁾
- Thermal Resistance: 0.85°C/W Junction to Case(Steady-State)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	150	A
Pulsed Drain Current ⁽³⁾	I_{DM}	450	A
Total Power Dissipation	P_D	147	W
Single Pulsed Avalanche Energy ⁽⁴⁾	E_{AS}	441	mJ

Note:

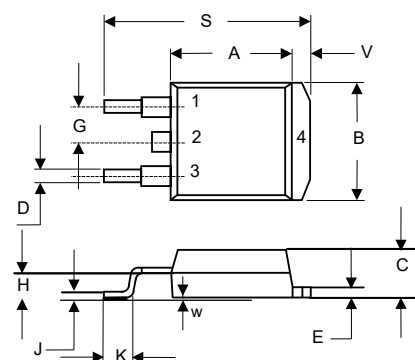
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ $t \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. $T_J = 25^{\circ}\text{C}$, $V_{DD} = 50\text{V}$, $L = 0.5\text{mH}$, $I_{AS} = 42\text{A}$

Internal Structure and Marking Code



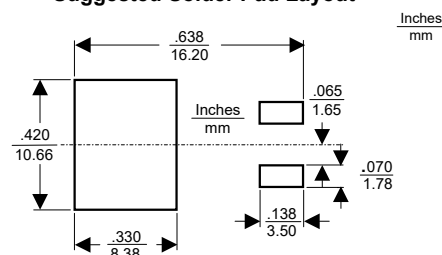
N-CHANNEL MOSFET

D²-PAK(TO-263)



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.331	0.370	8.40	9.40	
B	0.378	0.417	9.60	10.60	
C	0.165	0.189	4.20	4.80	
D	0.027	0.037	0.68	0.94	
E	0.045	0.055	1.14	1.40	
G	0.010		2.54		TYP.
H	0.096	0.134	2.43	3.40	
J	0.011	0.025	0.28	0.64	
K	0.071	0.131	1.80	3.32	
S	0.575	0.625	14.60	15.87	
V	0.042	0.058	1.07	1.47	
W	0.000	0.010	0.00	0.25	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		2.7	3.5	m Ω
		$V_{GS}=4.5V, I_D=20A$		3.5	4.8	m Ω
Gate Resistance	R_G	f=1MHz, Open drain		2		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				150	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$		0.8	1.3	V
Reverse Recovery Time	t_{rr}	$I_F=20A, dI_F/dt=500A/\mu s$		41.6		ns
Reverse Recovery Charge	Q_{rr}			39.8		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1MHz$		4650		pF
Output Capacitance	C_{oss}			850		
Reverse Transfer Capacitance	C_{riss}			65		
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=10V, I_D=25A$		71		nC
Gate-Source Charge	Q_{gs}			17		
Gate-Drain Charge	Q_{gd}			10.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=30V, V_{GEN}=10V, R_G=2\Omega, I_{DS}=25A$		15.9		ns
Turn-On Rise Time	t_r			55.2		
Turn-Off Delay Time	$t_{d(off)}$			57.5		
Turn-Off Fall Time	t_f			91.3		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

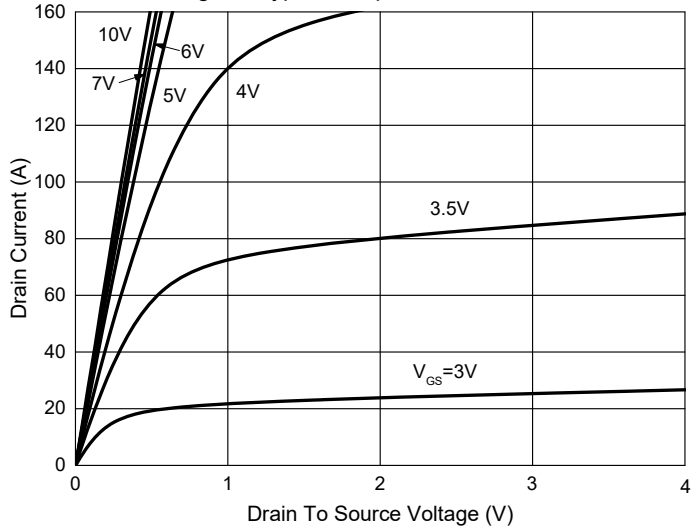


Fig. 2 - Transfer Characteristics

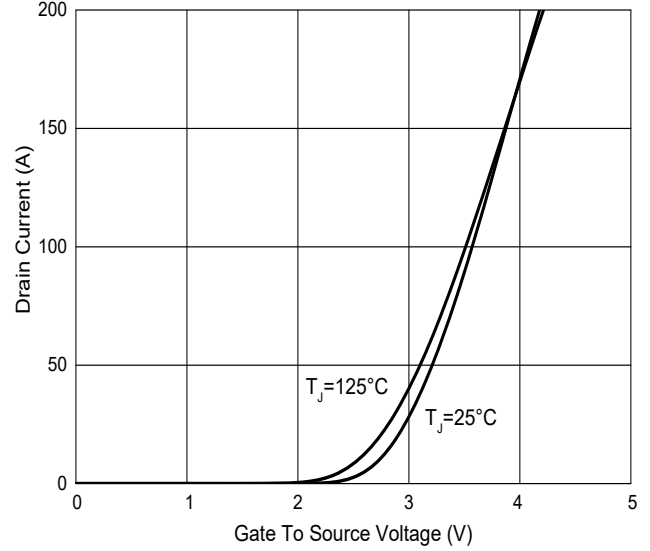


Fig. 3 - R_{DS(ON)} - I_D

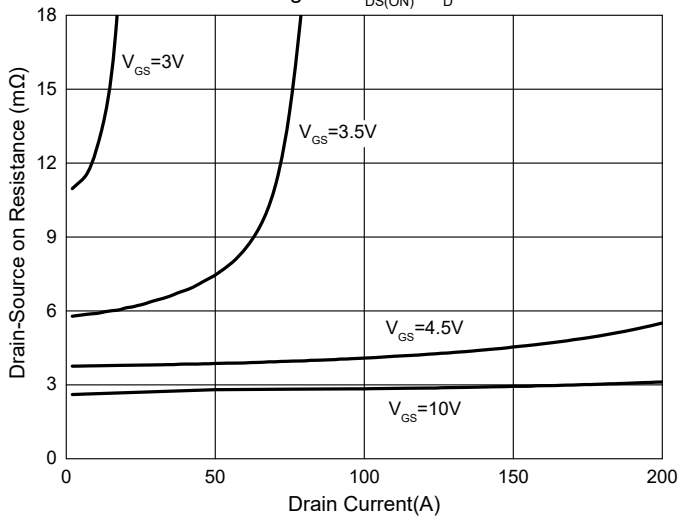


Fig. 4 - Drain-Source on Resistance

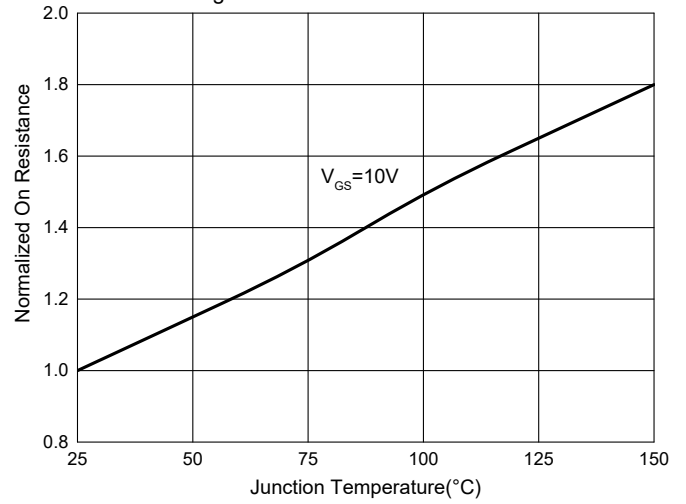


Fig. 5 - Capacitance Characteristics

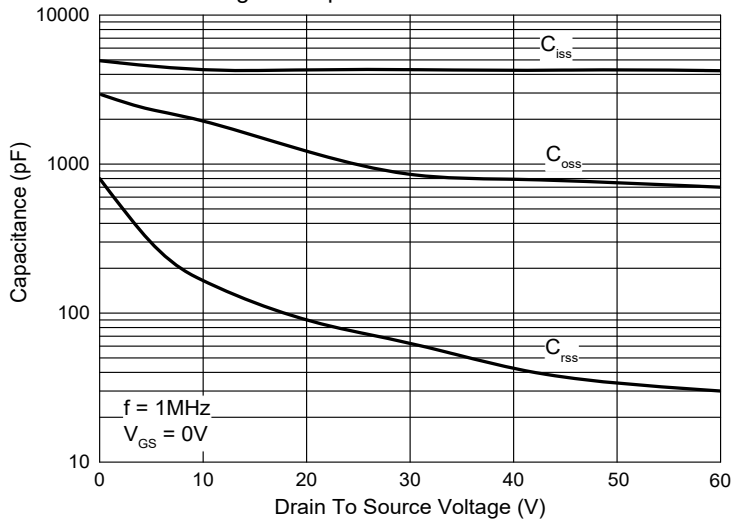
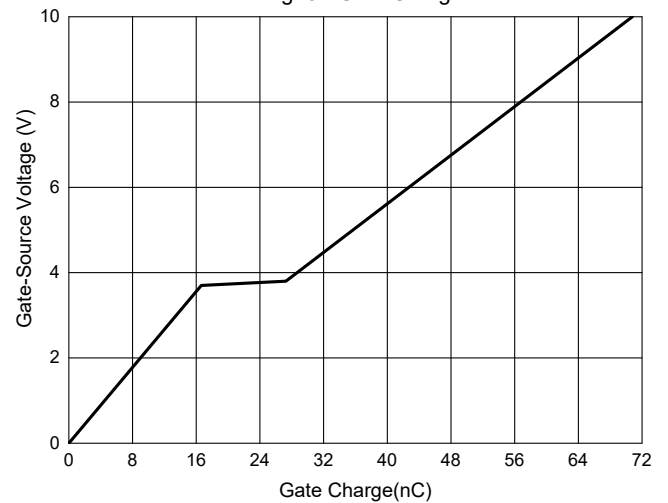


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area

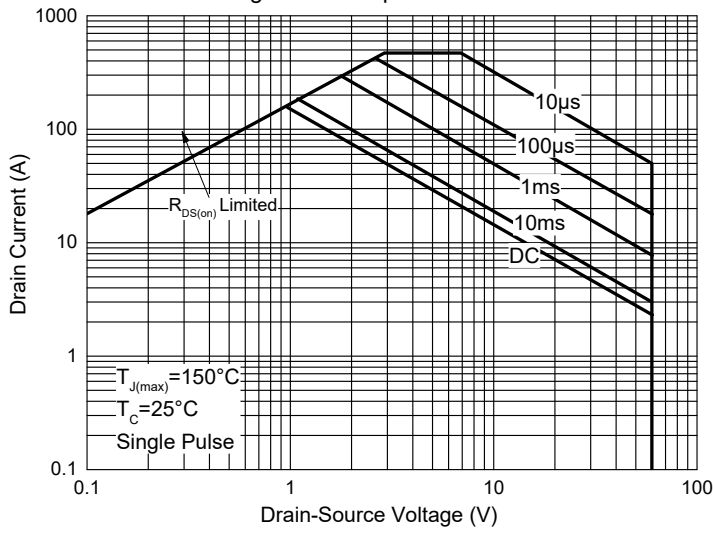
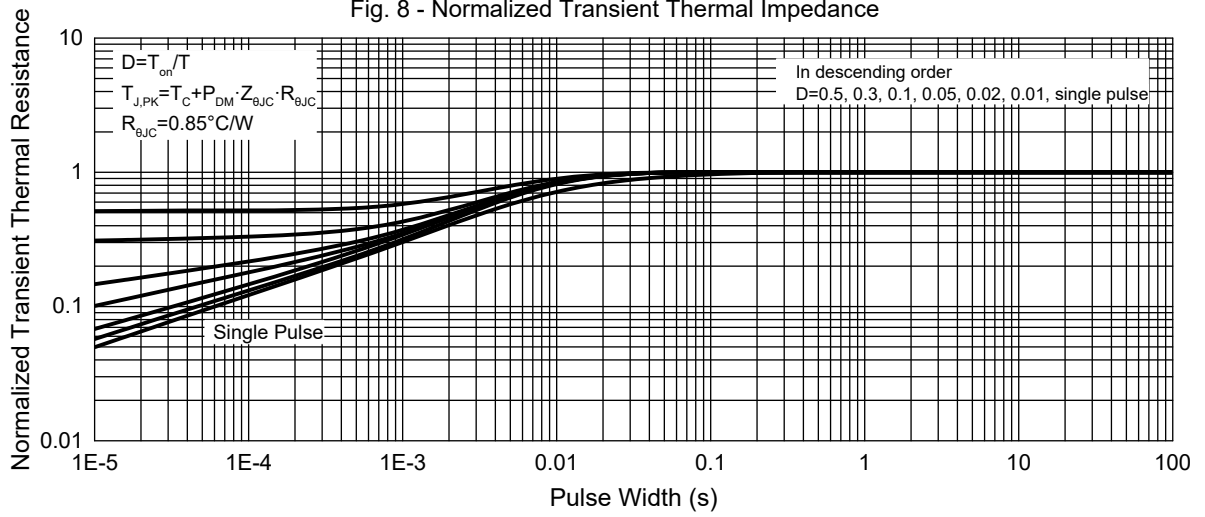


Fig. 8 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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